



|    |    |    |    |    |    |    |    |
|----|----|----|----|----|----|----|----|
|    |    |    |    |    |    |    |    |
| 00 | 08 | 10 | 18 | 20 | 28 | 30 | 38 |
|    |    |    |    |    |    |    |    |
| 01 | 09 | 11 | 19 | 21 | 29 | 31 | 39 |
|    |    |    |    |    |    |    |    |
| 02 | 0A | 12 | 1A | 22 | 2A | 32 | 3A |
|    |    |    |    |    |    |    |    |
| 03 | 0B | 13 | 1B | 23 | 2B | 33 | 3B |
|    |    |    |    |    |    |    |    |
| 04 | 0C | 14 | 1C | 24 | 2C | 34 | 3C |
|    |    |    |    |    |    |    |    |
| 05 | 0D | 15 | 1D | 25 | 2D | 35 | 3D |
|    |    |    |    |    |    |    |    |
| 06 | 0E | 16 | 1E | 26 | 2E | 36 | 3E |
|    |    |    |    |    |    |    |    |
| 07 | 0F | 17 | 1F | 27 | 2F | 37 | 3F |



40



48



50



58



60



68



70



78



41



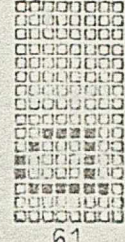
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51



59



61



69



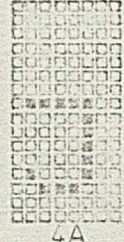
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79



42



4A



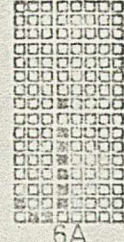
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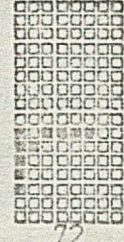
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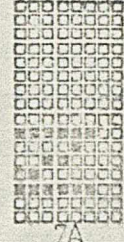
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6A



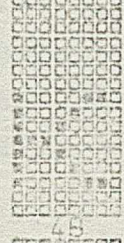
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7A



43



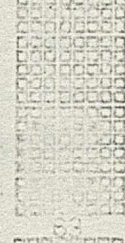
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53



5B



63



6B



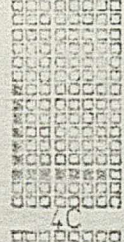
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7B



44



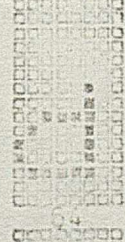
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54



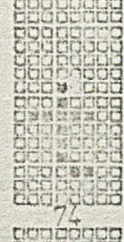
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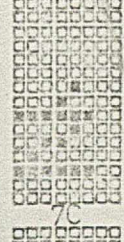
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6C



74



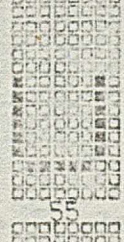
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45



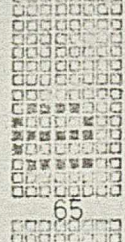
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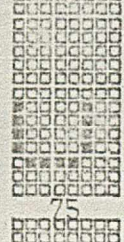
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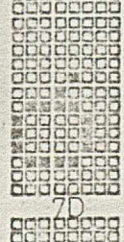
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6D



75



7D



46



4E



56



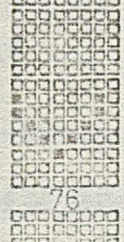
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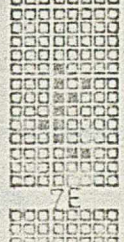
66



6E



76



7E



47



4F



57



5F



67



6F



77



7F

Wejścia "wyboru modułu" dla tej pamięci zaprogramowano w sposób następujący CS1 = 0, CS2 = 0, CS3 = 1.

Zestaw znaków generatora znaków MCY 7316N AE przedstawiono obok.

Dokumenty związane: TWT-82/CEMI-B10/B20. Cyfrowe mikroukłady scalone MOS. Pamięci stałe ROM MCY 7316N XX.

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